

## ABSTRACT

A method for chemical mechanical polishing of semiconductor substrates containing a metal layer requiring removal and metal interconnects utilizing a composition containing engineered copolymer molecules comprising hydrophilic functional groups and  
5 relatively less hydrophilic functional groups; the engineered copolymer molecules enabling contact-mediated reactions between the polishing pad surface and the substrate surface during CMP resulting in minimal dishing of the metal interconnects in the substrate.